

Title (en)  
SEMICONDUCTOR ARRANGEMENT OF MOSFETS

Title (de)  
HALBLEITERANORDNUNG VON MOSFETS

Title (fr)  
SYSTEME A SEMICONDUCTEURS DE MOSFET

Publication  
**EP 1878059 A1 20080116 (DE)**

Application  
**EP 06708511 A 20060224**

Priority  
• EP 2006060268 W 20060224  
• DE 102005019157 A 20050425

Abstract (en)  
[origin: DE102005019157A1] The arrangement has metal oxide semiconductor field effect transistors (MOSFETs) (Q1-Q6) on a chip that has connections (10, 12, 14) and serving as power and control cells. Source and gate connections of the MOSFETs are connected with each other and contact connections (10, 14), respectively. A drain connection of one power cell contacts the connection (12). Gate and drain connections of one control cell are connected with each other.

IPC 8 full level  
**H01L 29/78** (2006.01); **H01L 21/768** (2006.01)

CPC (source: EP KR US)  
**H01L 29/772** (2013.01 - KR); **H01L 29/7803** (2013.01 - EP US); **H01L 29/7813** (2013.01 - EP US); **H01L 21/76895** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

C-Set (source: EP US)  
**H01L 2924/0002 + H01L 2924/00**

Citation (search report)  
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Designated contracting state (EPC)  
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DOCDB simple family (publication)  
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**DE 102005019157 A 20050425**; EP 06708511 A 20060224; EP 2006060268 W 20060224; JP 2008508174 A 20060224; KR 20077024570 A 20060224; TW 95114033 A 20060420; US 91903206 A 20060224